Silicon NPN Power Transistors 2SC1079 2SC1080

DESCRIPTION

·With TO-3 package
·Complement to type 2SA679/680
·High power dissipation

APPLICATIONS

·For audio power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=?)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC1079	Open emitter	120	V
		2SC1080		100	
V_{CEO}	Collector-emitter voltage	2SC1079	Open base	120	V
		2SC1080		100	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			12	A
I_E	Emitter current			-12	A
P_C	Collector power dissipation		T_C=25?	100	W
T_j	Junction temperature			150	?
T_{stg}	Storage temperature			-65~150	?

CHARACTERISTICS

Tj=25? unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SC1079	I_C=0.1A ;I_B=0	120			V
		2SC1080		100			
$V_{(BR)EBO}$	Emitter-base breakdown voltage		I_E=10mA ;I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage		I_C=10A; I_B=1A			3.0	V
V_{BE}	Base-emitter on voltage		I_C=10A ; V_{CE}=5V			2.5	V
I_{CBO}	Collector cut-off current		V_{CB}=50V; I_E=0			0.1	mA
I_{EBO}	Emitter cut-off current		V_{EB}=5V; I_C=0			0.1	mA
h_{FE-1}	DC current gain		I_C=2A ; V_{CE}=5V	40		140	
h_{FE-2}	DC current gain		I_C=7A ; V_{CE}=5V	15			
f_T	Transition frequency		I_C=2A ; V_{CE}=5V		4		MHz

u **h_{FE-1} Classifications**

R	Y
40-80	70-140

PACKAGE OUTLINE

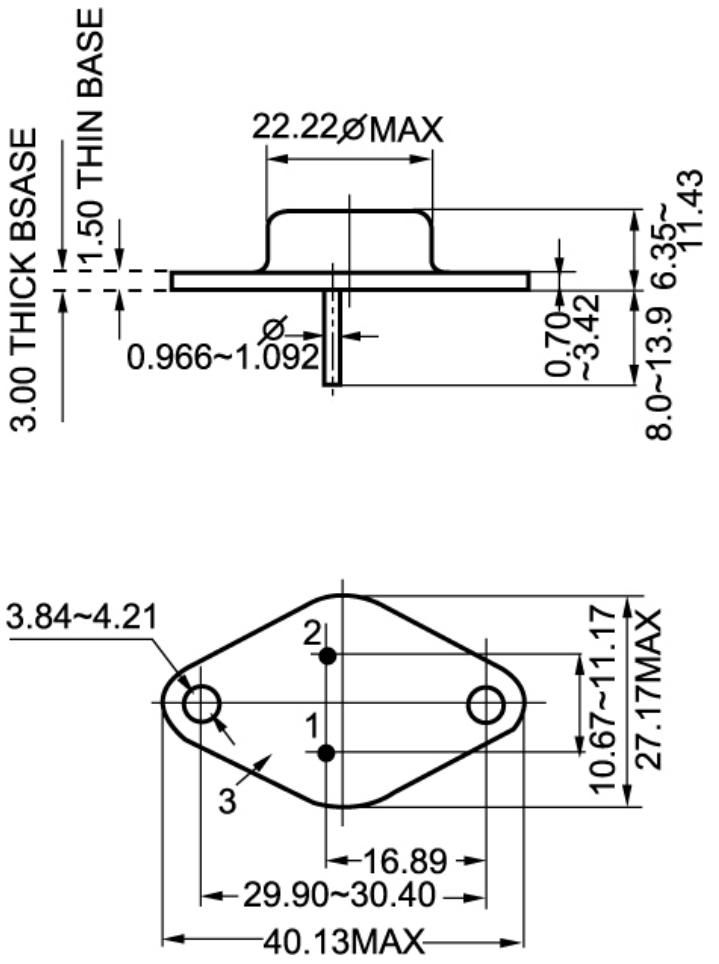

Fig.2 outline dimensions (unindicated tolerance:±0.1mm)